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Docket No. SUN-DA-1381

Serial No. 10/757,821

In the Claims

This listing of claims will replace all prior versions, and listings, of claims in the application.

1. (Currently Amended) A method of making a monitoring pattern of a shallow trench isolation profile, comprising:

forming a first pattern on a substrate to monitor a depth of a first shallow trench isolation, and wherein the first pattern includes a plurality of ~~unequally-spaced~~ active regions on the substrate, ~~wherein distances between the plurality of active regions are unequally spaced~~; and

forming a second pattern on the substrate to measure electrical effects associated with a depth and a profile of a second shallow trench isolation, wherein the second pattern includes a plurality of equally spaced active regions on the substrate, a plurality of contact regions that electrically connect the equally spaced active regions, and a plurality of gates that are formed on the equally spaced active regions, wherein the gates do not contact the first pattern.

2. (Original) The method as defined by claim 1, wherein the depth, the profile and the electrical effects are monitored according to density and size of the first and second patterns.

3. (Original) The method as defined by claim 1, wherein the depth and the profile are monitored using a single monitoring pattern.